

# BS Elektronik Service GmbH

## AlGaInP/Si Red Orange Chip ---540UOH

### 1. Scope

- AlGaInP High- Brightness LED chip.

### 2. Structure

- AlGaInP on Silicon
- N Electrode (cathode) side : Gold.
- P Electrode (anode) side : Gold alloy.

### 3. Size

- Chip size : 40 mil × 40 mil (1mm × 1 mm)
- Pattern drawing : per fig. 1

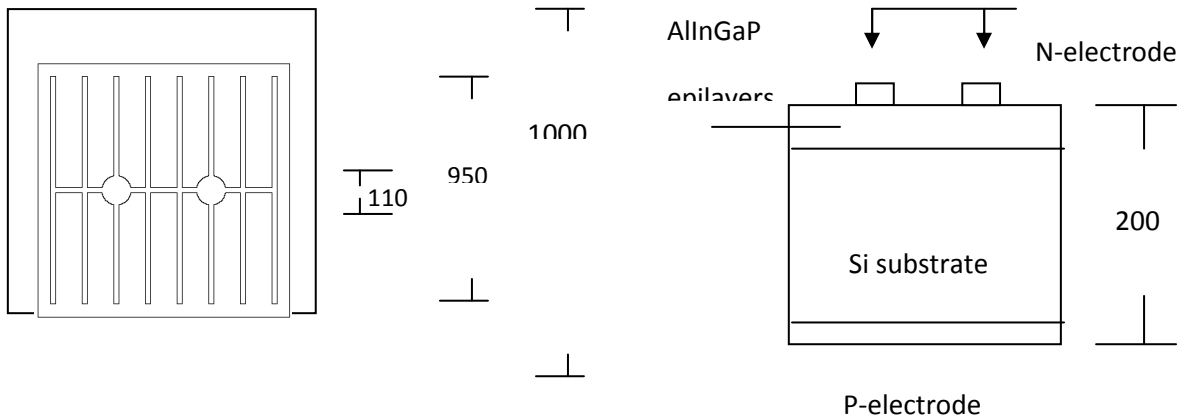
### 4. Electro-Optical Characteristics

(Ta = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F = 350 \text{ mA}$		2.5		V
Reverse Voltage	$I_R$	$I_R = 10 \text{ V}$			10	$\mu\text{A}$
Luminous Intensity	$I_v$	$I_F = 350 \text{ mA}$	※			mcd
Wavelength	$\lambda_d$	$I_F = 20 \text{ mA}$	620	625	630	nm
Spectrum Width of Half Value	$\Delta \lambda$	$I_F = 20 \text{ mA}$		20		nm

\* R:  $\geq 4300$ , S:  $\geq 5000$ , T:  $\geq 5700$ , U:  $\geq 6500$

**Maximum reverse-biased voltage < 60V; therefore,  $V_z$  test is forbidden.**



Recommendation for bonding condition:

— bonding force 40 g, bonding temperature 280C, bonding time 20 ms.